

Title (en)
Semiconducting device mounting.

Title (de)
Montage einer Halbleiteranordnung.

Title (fr)
Montage d'un dispositif semi-conducteur.

Publication
EP 0335744 B1 19941026 (EN)

Application
EP 89303227 A 19890331

Priority
GB 8807729 A 19880331

Abstract (en)
[origin: EP0335744A1] A technique for assembling semiconductor devices in which semiconductor elements, especially lasers or LEDS, are mounted on a first packaging element such as a heat spreader that is mounted on a second packaging element such as a heat sink. Handling of solder preforms is avoided by coating at least one of each of the pairs of surfaces to be brought into contact with a layer of solder and heating the assembly to melt both solder layers in a single operation. In a preferred embodiment a heat spreader is coated in solder on both sides and interposed between a semiconductor element and a heat sink and the assembly is heated. Molybdenum may be used as a layer to aid wetting and adhesion and gold/tin solder may be used. Slightly different solidification temperatures and compositions for the layers may result from different take up of metallisation layers from the components into the solder.

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IPC 8 full level
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